

SANYO	No.3398A	2SA1772/2SC4615
		2SA1772:PNP Epitaxial Planar Silicon Transistor 2SC4615:NPN Triple Diffused Planar Silicon Transistor
High Voltage Driver Applications		

Features

- Large current capacity ($I_C = 1A$)
- High breakdown voltage ($V_{CEO} \geq 400V$)

(): 2SA1772

Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Collector to Base Voltage	V_{CBO}	(-) 400	V
Collector to Emitter Voltage	V_{CEO}	(-) 400	V
Emitter to Base Voltage	V_{EBO}	(-) 5	V
Collector Current	I_C	(-) 1	A
Collector Current(Pulse)	I_{CP}	(-) 2	A
Collector Dissipation	P_C	1	W
		15	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to $+150$	$^\circ C$

$T_c = 25^\circ C$

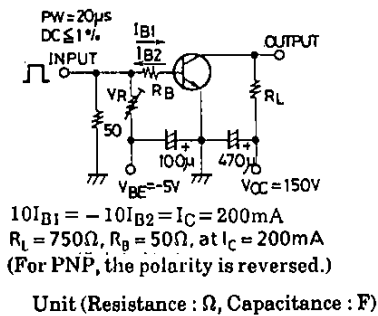
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)300V, I_E = 0$		(-) 1.0		μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$		(-) 1.0		μA
DC Current Gain	h_{FE}	$V_{CE} = (-)10V, I_C = (-)100mA$	40^*		200^*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)10V, I_C = (-)50mA$		(50) 70		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)200mA, I_B = (-)20mA$		(-) 1.0		V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)200mA, I_B = (-)20mA$		(-) 1.0		V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-) 400			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-) 400			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-) 5			V
Output Capacitance	C_{ob}	$V_{CB} = (-)30V, f = 1MHz$		(12) 8		pF
Turn-ON Time	t_{on}	See specified Test Circuit.	(0.25) 0.11			μs
Storage Time	t_{stg}		(3.0) 4.0			μs
Fall Time	t_f		(0.3) 0.65			μs

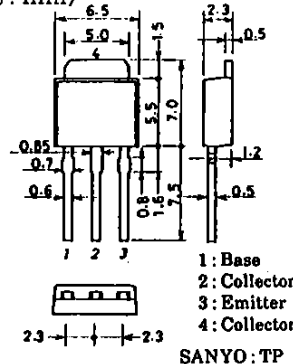
*: The 2SA1772/2SC4615 are classified by 100mA h_{FE} as follows:

40 C 80	60 D 120	100 E 200
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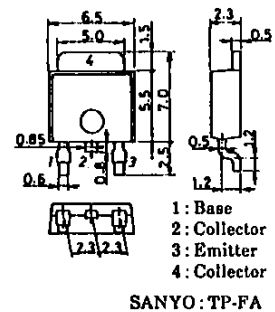
Switching Time Test Circuit



Package Dimensions 2045B
(unit : mm)



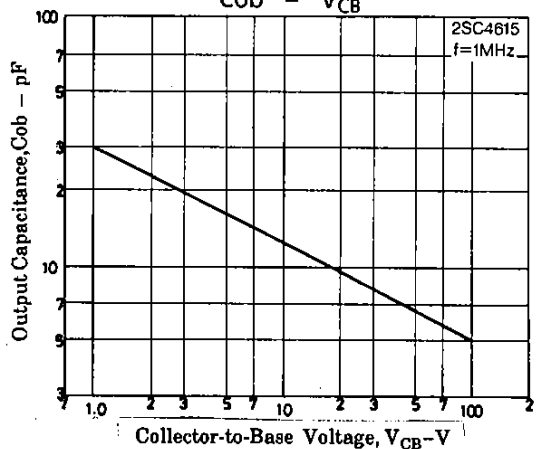
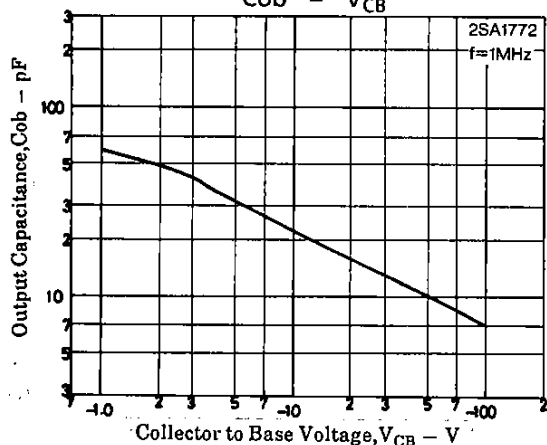
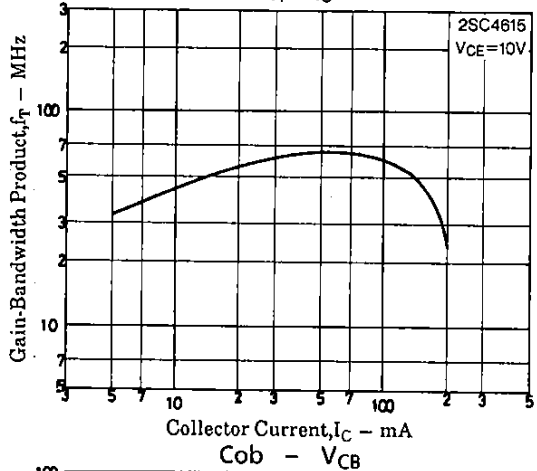
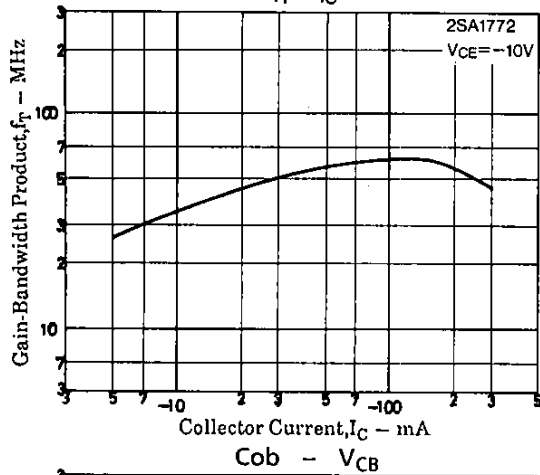
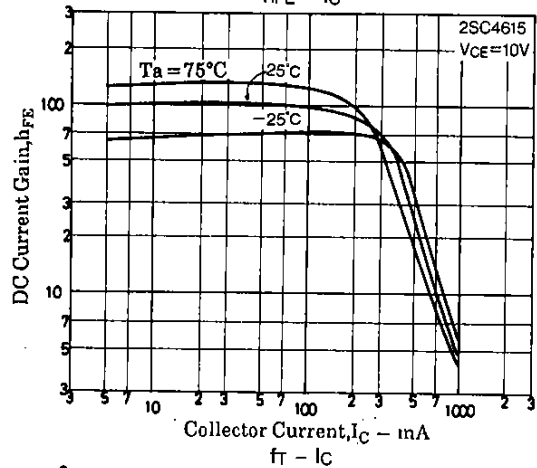
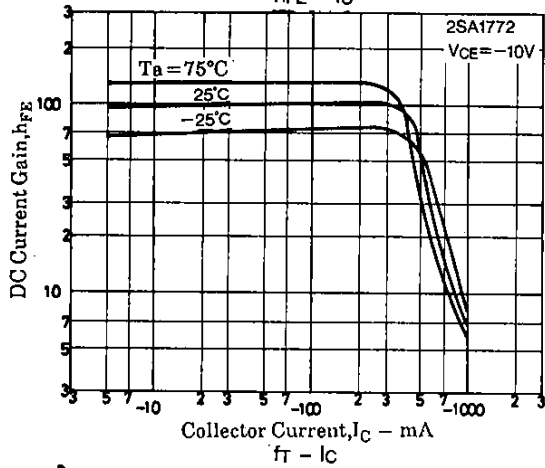
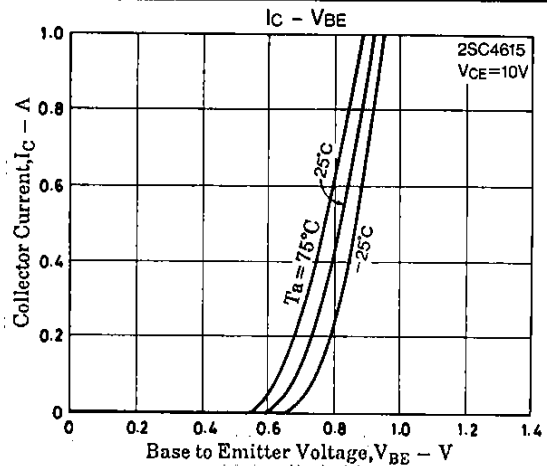
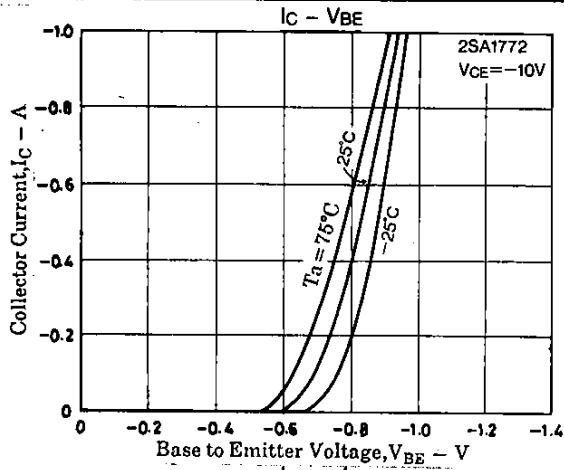
Package Dimensions 2044B
(unit : mm)



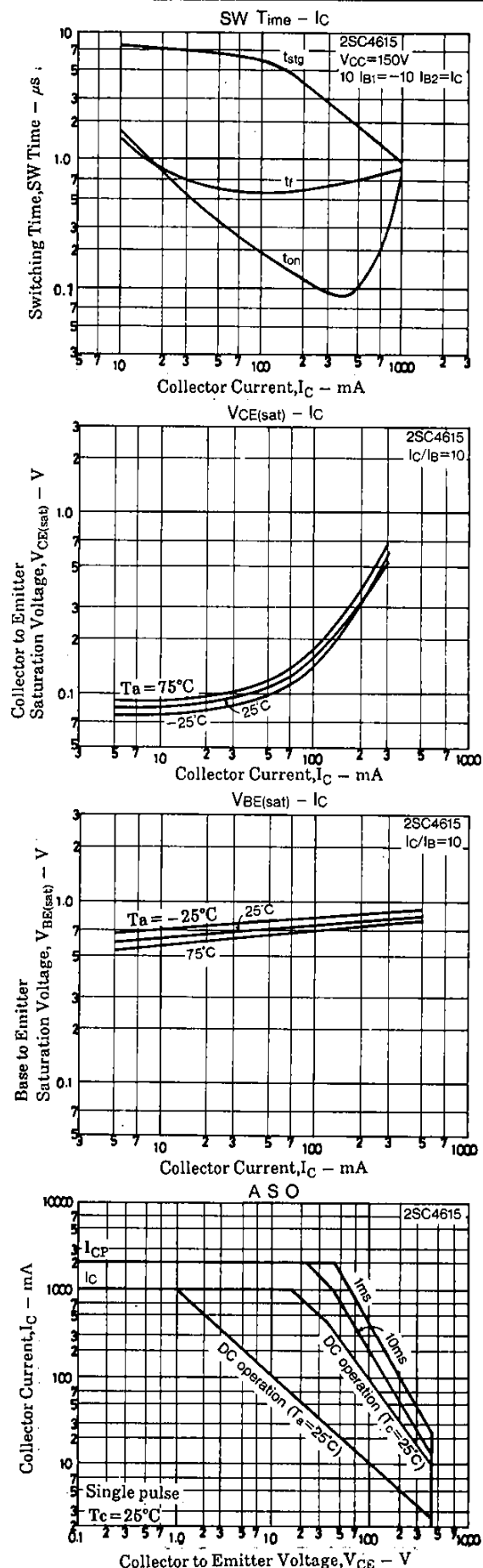
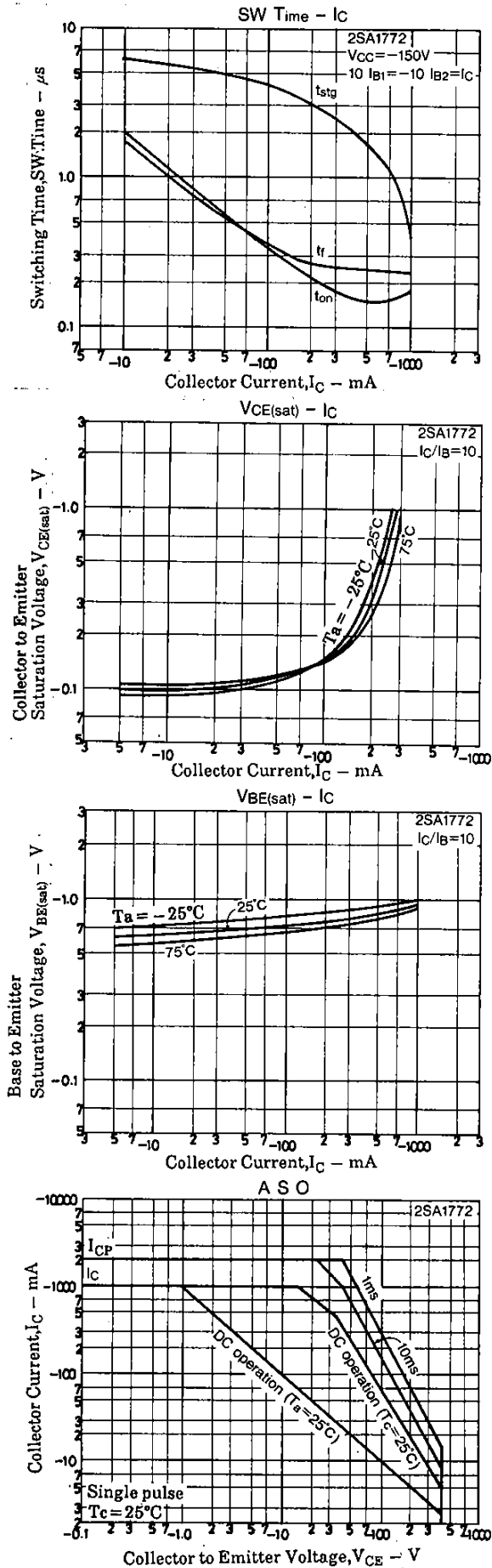
SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

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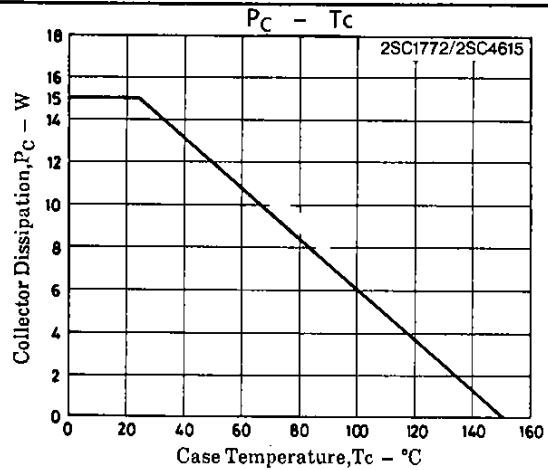
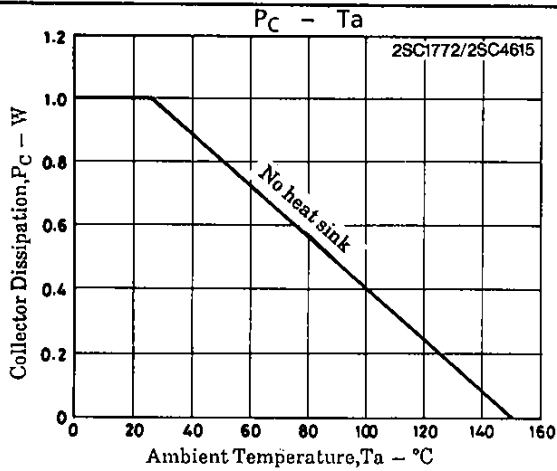
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